Schottky Barrier Diode

RB060M-40DD

Datasheet

AEC-Q101 Qualified

●Applications

General rectification

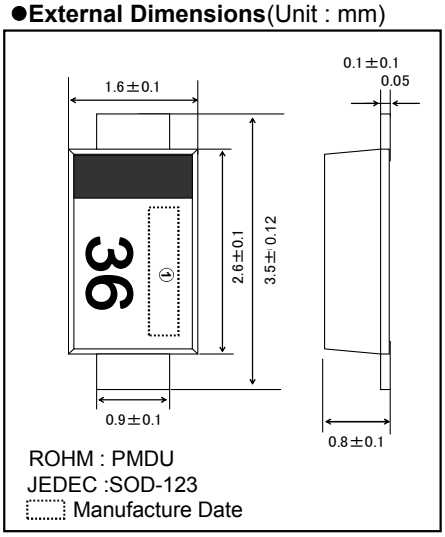
●Features

1)Small power mold type.(PMDU)
2)High reliability

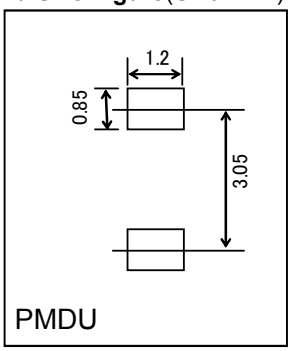
●Construction

Silicon epitaxial

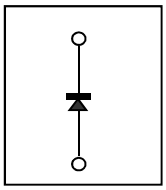
●External Dimensions(Unit : mm)



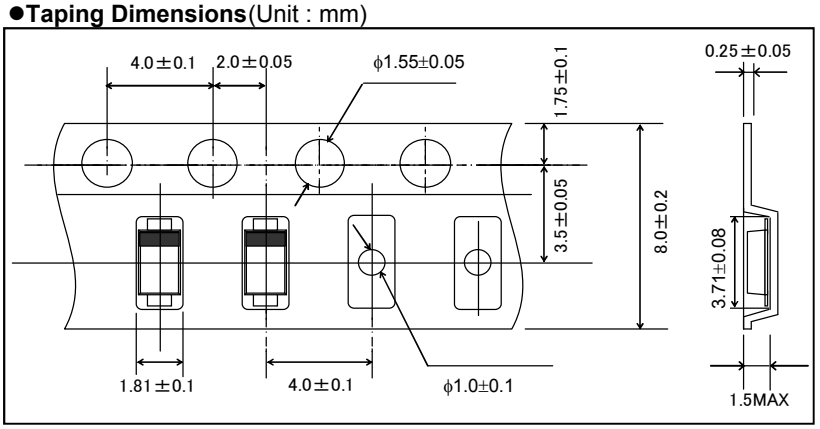
●Land Size Figure(Unit : mm)



●Structure



●Taping Dimensions(Unit : mm)



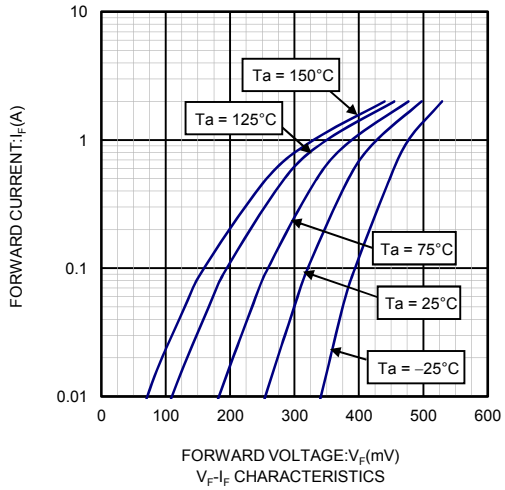
●Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive)	V_{RM}	40	V
Reverse voltage (DC)	V_R	40	V
Average rectified forward current (*1)	Io	2	A
Forward current surge peak (60Hz・1cyc)	I_{FSM}	30	A
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

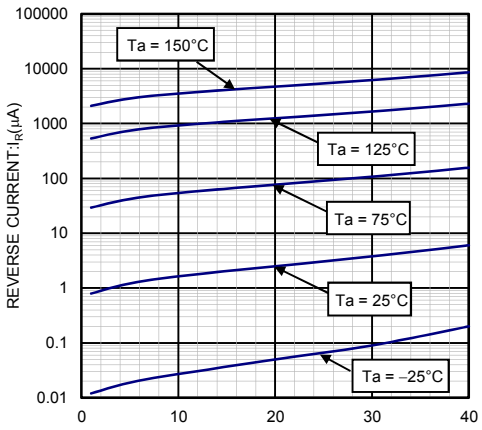
(*1)Mounting on epoxi board. 180°Half sine wave

●Electrical Characteristics(Ta=25°C)

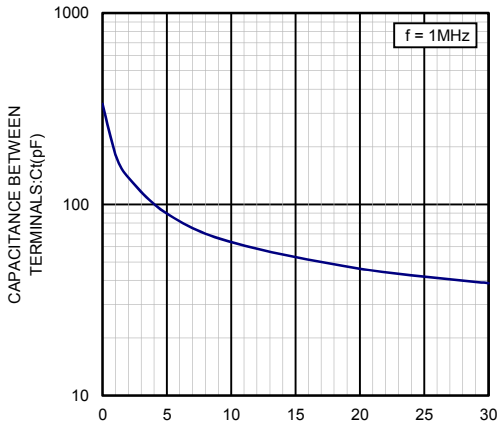
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	–	0.56	V	I_F=2.0A
Reverse current	I_R	–	–	500	μA	V_R=40V



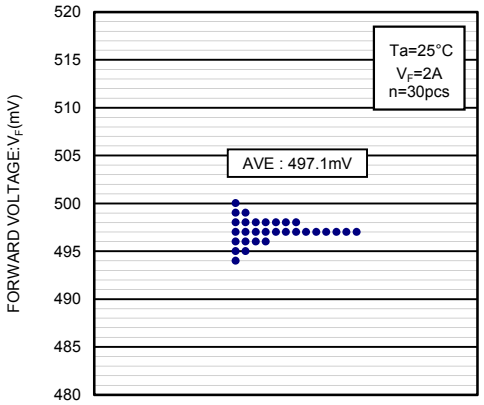
VF-IF CHARACTERISTICS



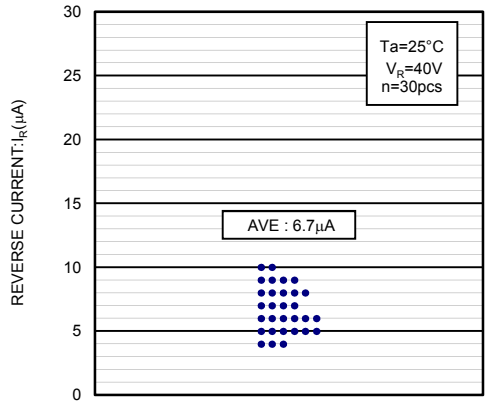
VR-IR CHARACTERISTICS



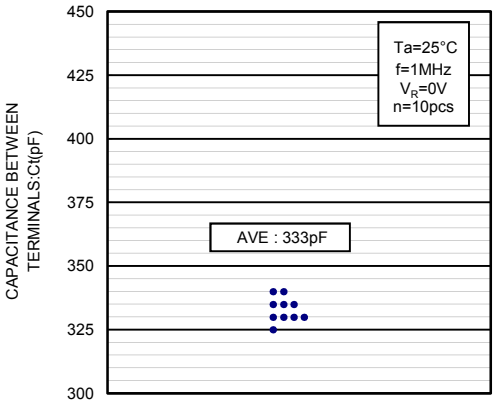
VR-Ct CHARACTERISTICS



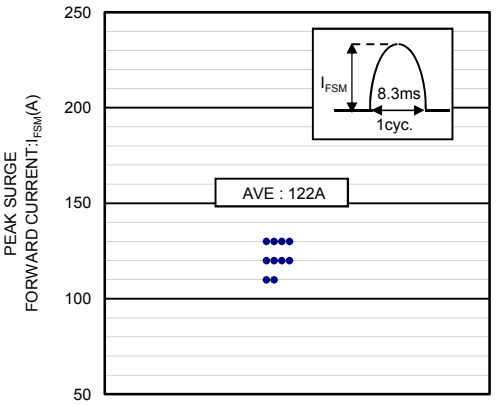
VF DISPERSION MAP



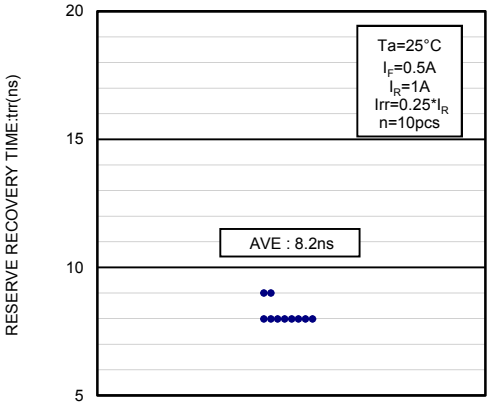
IR DISPERSION MAP



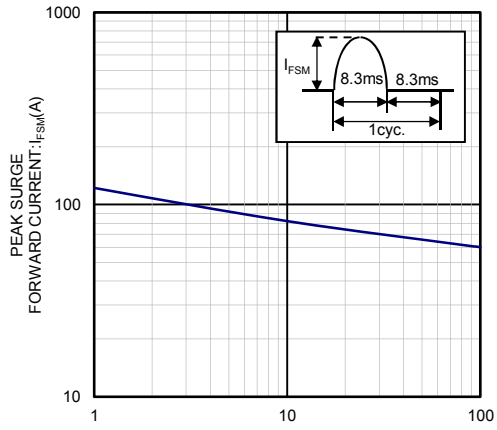
Ct DISPERSION MAP



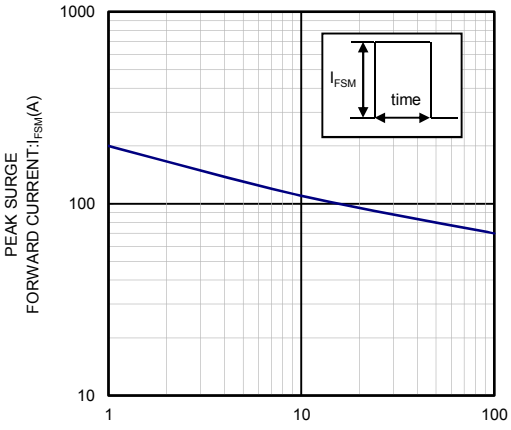
I_{FSM} DISRESION MAP



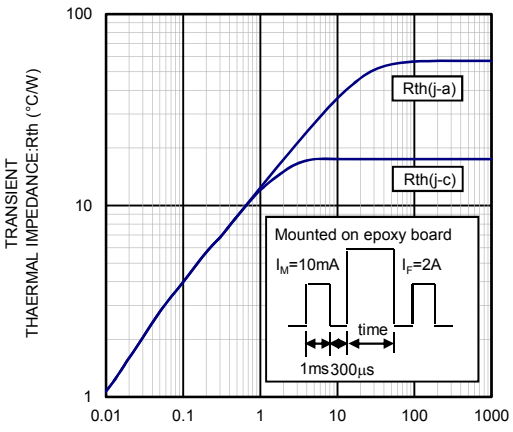
trr DISPERSION MAP



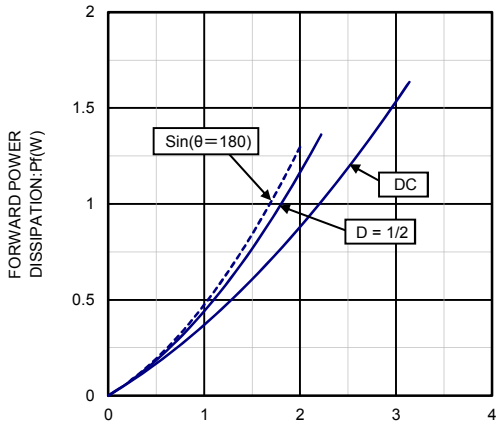
NUMBER OF CYCLES
I_{FSM}-CYCLE CHARACTERISTICS



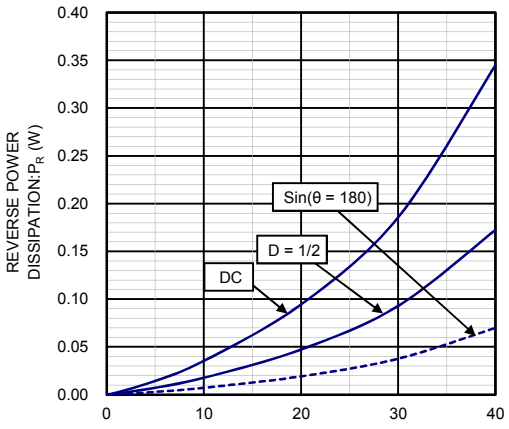
TIME:t(ms)
I_{FSM}-t CHARACTERISTICS



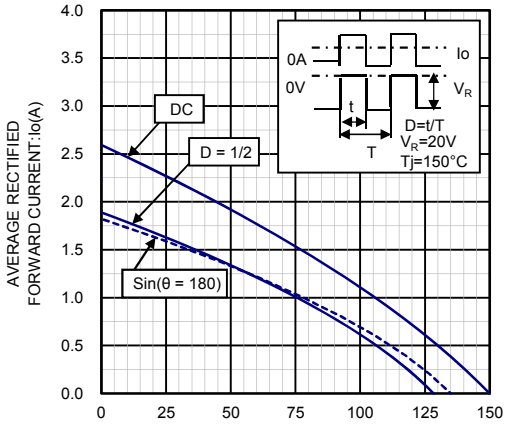
TIME:t(s)
Rth-t CHARACTERISTICS



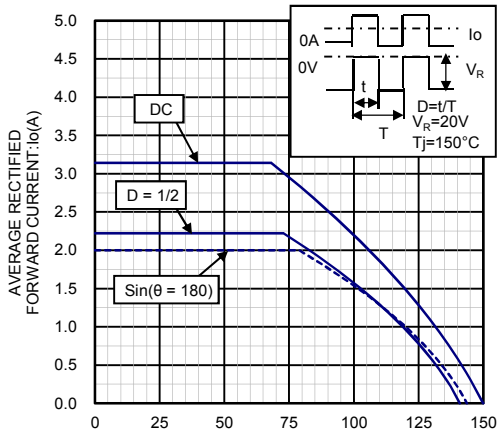
AVERAGE RECTIFIED
FORWARD CURRENT:Io(A)
Io-Pf CHARACTERISTICS



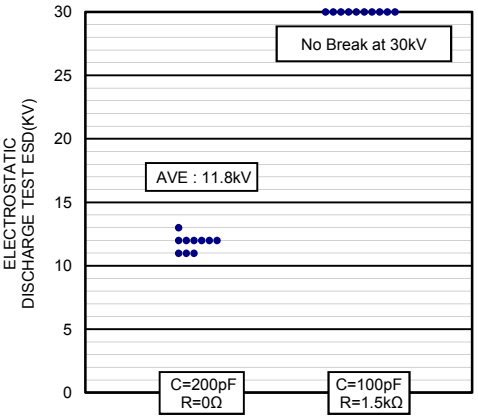
REVERSE VOLTAGE:V_R(V)
V_R-P_R CHARACTERISTICS



AMBIENT TEMPERATURE:Ta(°C)
DERATING CURVE(Io-Ta)



CASE TEMPARATURE:Tc(°C)
DERATING CURVE(Io-Tc)



ESD DISPERSION MAP